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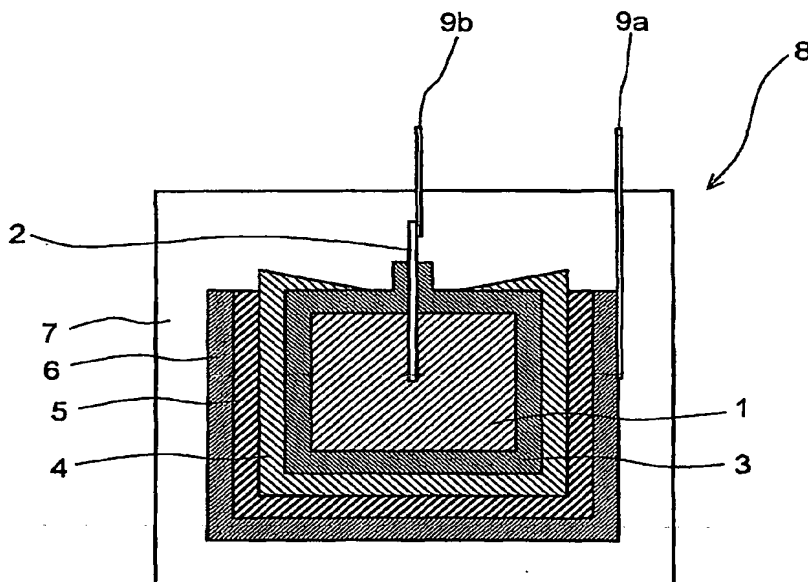
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(54) Title: **SOLID ELECTROLYTE CAPACITOR**



(57) Abstract: The present invention relates to a solid electrolyte capacitor having a small size, a high capacitance, a low ESR and an excellent LC value, which comprises a jacketed capacitor element obtained by sequentially stacking a dielectric oxide film layer, a semiconductor layer and an electrically conducting layer on a surface of a valve-acting metal sintered body or electrically conducting oxide sintered body connected with an anode lead, wherein the thickness of the semiconductor layer in the vicinity of the anode lead-connection point on the sintered body face connected with an anode lead is 5 μ m or less, and also relates to an electronic circuit and electronic device using the capacitor.



SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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